

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	31.2942	N/A	16.3442
RT2	9.7429	N/A	5.8412
RT3	28.1521	N/A	6.4092
RT4	55.4874	N/A	16.6502
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	2.4022 m	N/A	1.4474 m
CT2	291.0281 u	N/A	165.7211 u
CT3	33.3082 m	N/A	159.1680 m
CT4	1.3175	N/A	4.0724 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	15.6106	N/A	9.3126
RF2	32.9349	N/A	21.7163
RF3	25.5324	N/A	8.4387
RF4	52.7888	N/A	5.5442
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	310.9572 u	N/A	170.4864 u
CF2	2.7712 m	N/A	1.1574 m
CF3	45.0379 m	N/A	1.9990 m
CF4	1.3696	N/A	191.7478 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

